

Appl. No. 10/650,504
Amdt. Dated September 27, 2006
Reply to Office Action of June 28, 2006

Attorney Docket No. 81872.0052
Customer No.: 26021

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-12. (Canceled)

13. (Currently amended): A dry etching method for etching a surface of a substrate to be etched, said method comprising:

placing a substrate to be etched on an electrode inside a chamber, wherein a part of said chamber is connected to a ground; and

covering said substrate to be etched with a plate between said part of said chamber and said electrode, wherein said plate is provided with a number of opening portions,

wherein a distance between a surface opposing said substrate to be etched and said substrate to be etched in a peripheral portion of said plate is set shorter than a distance between ~~the~~ said surface opposing said substrate to be etched and said substrate to be etched in a central portion of said plate.

14. (Original): The dry etching method according to claim 13, wherein said dry etching method is a reactive ion etching method.

15.-19. (Canceled)

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20. (Currently amended): A dry etching method etching a surface of a substrate to be etched, said method comprising:

placing a substrate to be etched on an electrode inside a chamber, wherein a part of said chamber is connected to a ground, - and

covering said substrate to be etched with a plate provided with a number of opening; and [L]

forming fine textures on a surface of said substrate to be etched by applying RF power to said electrode.

wherein a protruding wall is provided to said plate on a surface opposing said substrate to be etched and said protruding wall is separated from a nearest surface of said substrate by a gap space.

21. (Original): The dry etching method according to claim 20, wherein said dry etching method is a reactive ion etching method.

22.-23. (Canceled)